

Developments of miniature atomic clocks based on Coherent Population Trapping

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FEMTO-ST Institute, Besançon, France

Context

The performances of numerous systems directly depend on the time or frequency reference they use.

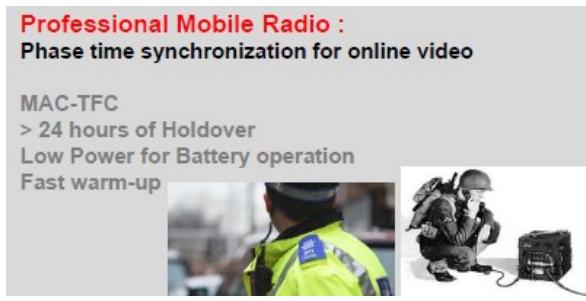
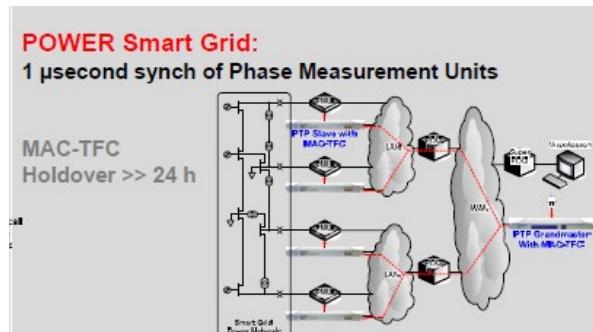
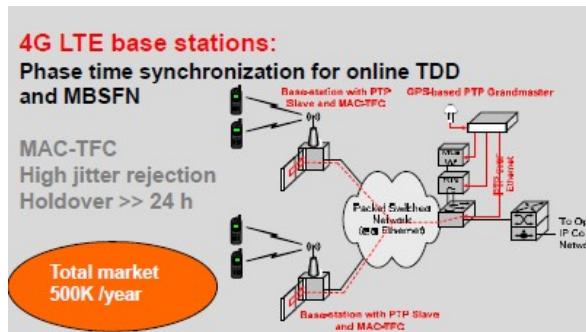
Objectives:

Current technology = quartz crystal oscillators → reach their limit

Develop a portable, battery-powerable, stable and cheap time reference : Miniature atomic clock

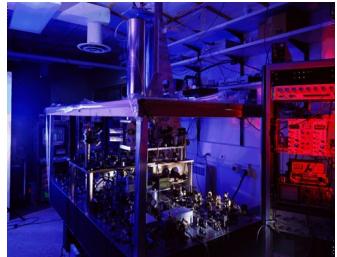
- Specifications :**
- Total volume: 10 cm³
 - Power consumption: 100-150 mW
 - Frequency stability performances: 10-11 @ 1h and 1 day integration (1 µs/day)

Applications:



Context

Goal: Bring atomic timing to the size and power range previously covered by quartz oscillators



Cs Primary standard



Commercial Cs beam clock



Compact atomic clock



Miniature Atomic clock



Precision quartz



Wristwatch quartz

Accuracy: 10-15

10-13

10-11

10-10

10-5

Timing error: 10ns / year

10μs / year

0.1μs / day

100μs / day

1s / day

Size: 107 cm³

104 cm³

102 cm³

1-10 cm³

10 mm³

Power: kW

100's W

1 W

100 mW

10 μW

Cost: >1M\$

50k\$

2k\$

100\$

1\$

Frequency stab: 10-14

Few 10-12

10-11

10-10

10-10

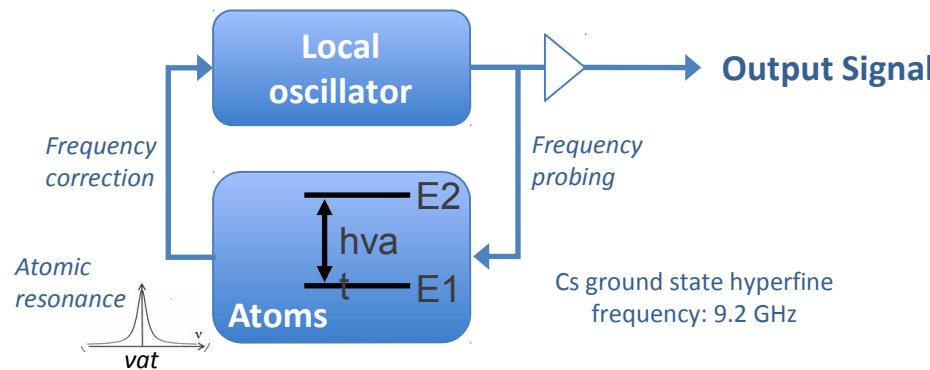
10-9

Decreasing performance/size/power/cost

Principle

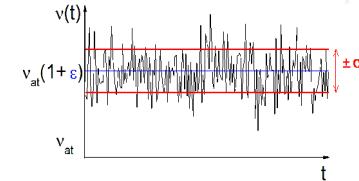


Atomic clock: Lock the frequency of a local oscillator onto an atomic transition frequency



Accuracy

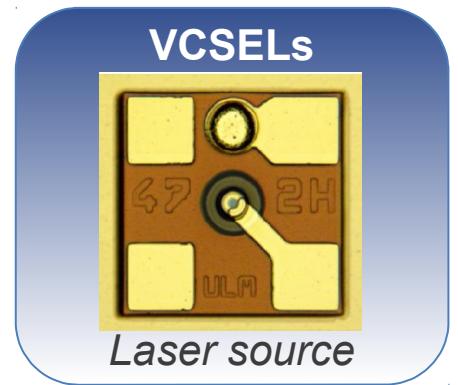
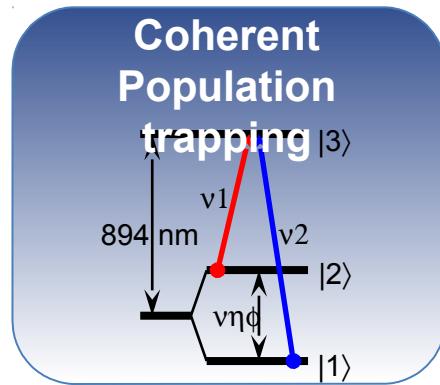
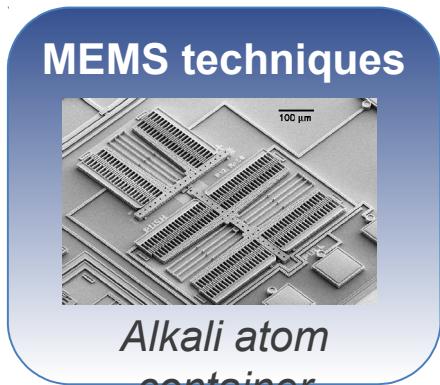
$$v_{osc} = v_{at} (1 + \varepsilon + y(t))$$



Frequency stability: signal relative frequency fluctuations (Allan deviation)

$$\sigma_y(\tau) = \frac{\Delta v}{v_0} \frac{1}{S/N} \tau^{-\frac{1}{2}}$$

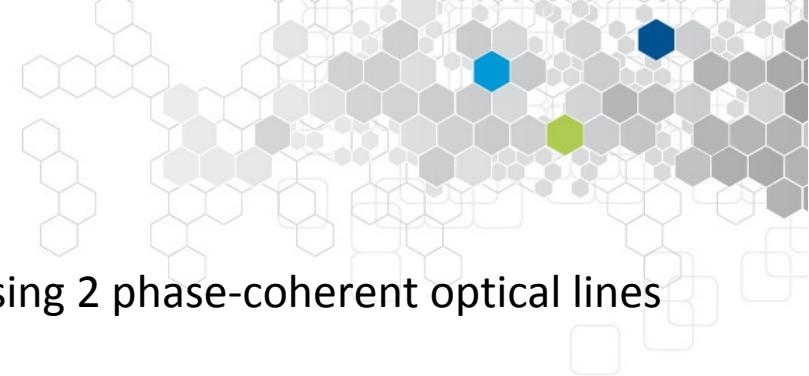
How to miniaturize such a clock?



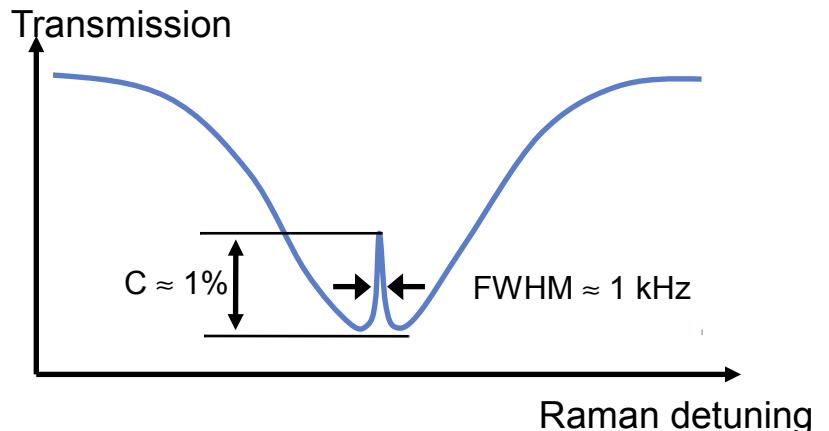
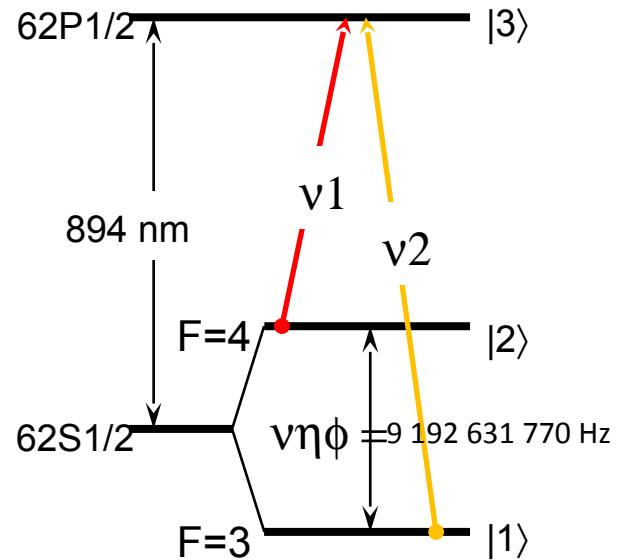
« All-optical » atomic clock – No resonant cavity

Extreme miniaturization

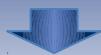
CPT Principle



2 long-lived ground states connected to a common excited state using 2 phase-coherent optical lines



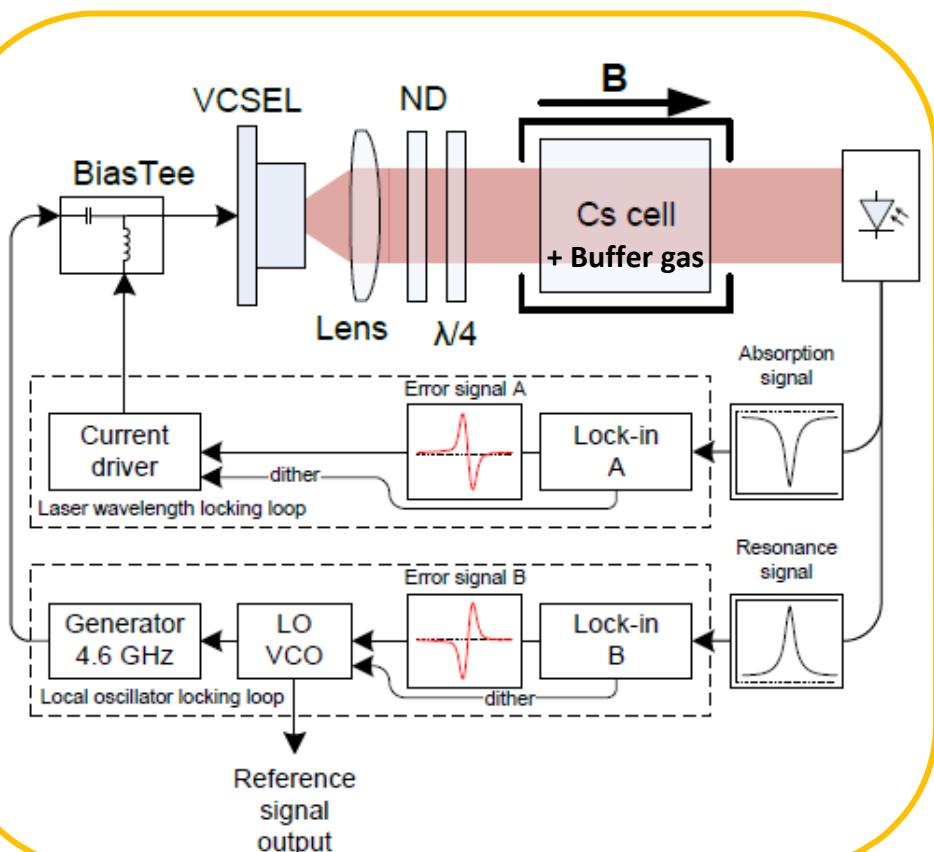
Frequency splitting = ground-state hyperfine splitting



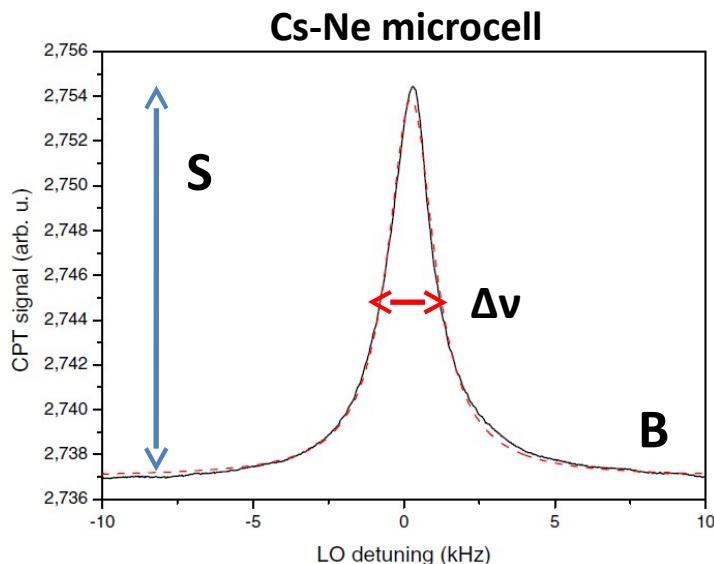
Dark state = CPT state : The transparency of the atomic vapor is increased

All-optical interrogation : No microwave resonant cavity → miniaturization

Miniature CPT clock



- Alkali vapor cell:**
 - Strong sealing for long term operation
 - Pure atmosphere filled with Cs and buffer gas at target pressure
- Laser:**
 - 2 lines at $\lambda=894.6\text{nm}$ (D1) splitted by 9.2 GHz (Bias Current modulation)
 - Shaped beam (collimated)
 - Circular polarization state
- Packaging/Electronics:**
 - Including thermal control, magnetic field generation, local oscillator, optical beam shaping, etc.



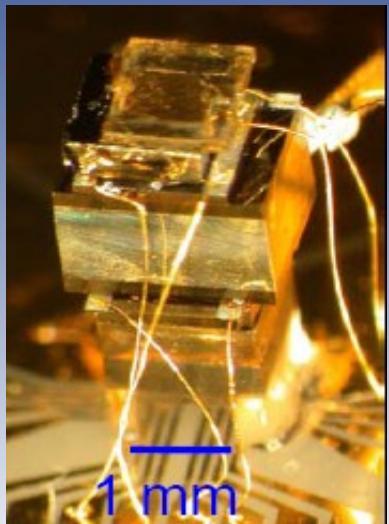
$$C = \frac{S}{B}$$

$$\sigma_y(\tau) = \frac{\Delta v}{v_0} \frac{1}{S/N} \tau^{-\frac{1}{2}}$$

State of the art

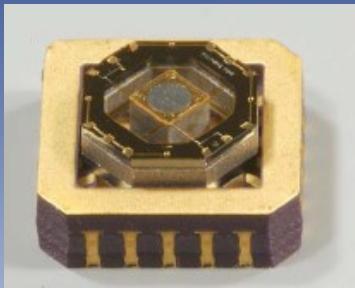


NIST 2004



First world CSAC prototype

2007



16 cm³
115 mW
2 10-10 at 1s
10 MHz output

SYMMETRICOM

2011

Symmetricom®



First commercially-available CSAC

Need for a European chip-scale atomic clock

Innovative scientific and technological solutions for high-performance

Initiated by FEMTO-ST in 2005



MAC-TFC Project in 2009

Projects



 MAC-TFC
Collaborative project
2009-2012

 SEVENTH FRAMEWORK PROGRAMME

10 industrial and academic partners

 Coordinator



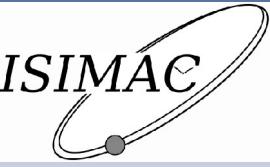










 ISIMAC
ASTRID project
2012-2015




2 academic partners

 Coordinator


Systèmes de Référence Temps-Espace

Microfabricated cells - Buffer gas selection

Operation in the Dicke regime → kHz-linewidth in mm-scale cells

Issue: Temperature-dependent frequency shift of the clock transition

1st option:

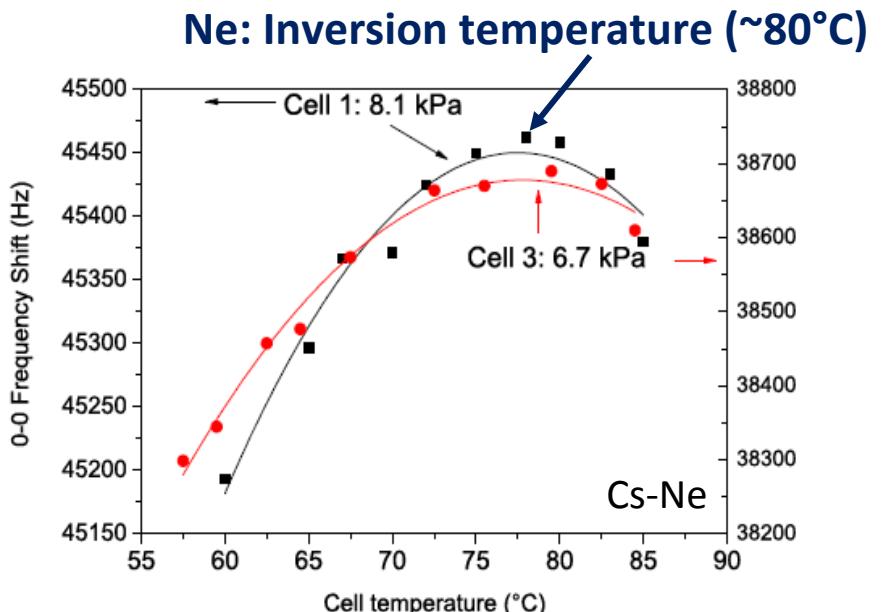
$$\Delta v_{bg} = P_0 [\beta + \delta(T - T_0) + \gamma(T - T_0)^2]$$

Buffer gas mixture with appropriate partial pressures for compensation

- Difficult to control (especially in microcells)
- Coefficients poorly known or wide dispersion

No mixtures required → relaxed constraints on the buffer gas pressure control

Ne buffer gas is a good candidate for Cs miniature clocks



D. Miletic et al., Elec. Lett., 2010

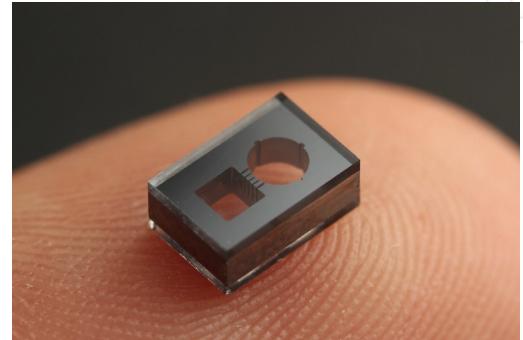
R. Boudot et al., Journ. Appl. Phys., 2011

Microfabricated alkali cells - Technology

Requirements: Cs Cell with pure atmosphere and long term hermicity
- Collectively fabricated

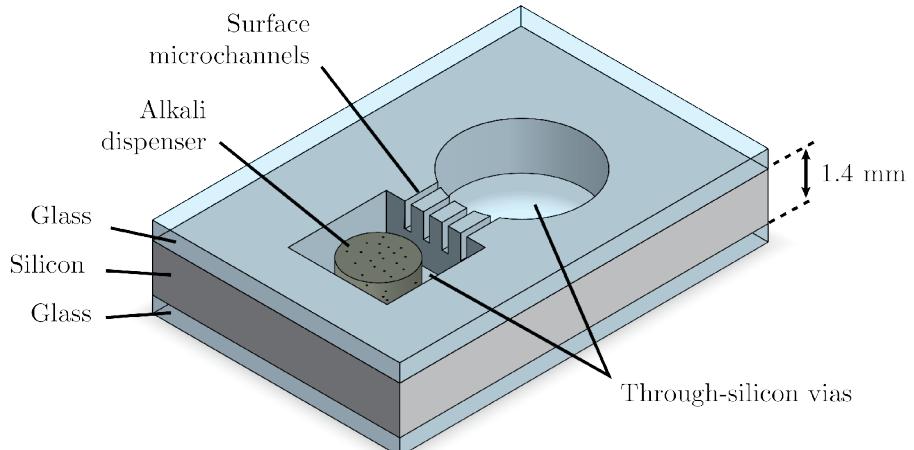
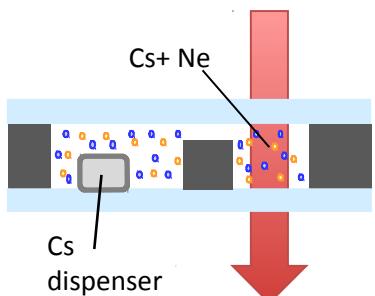
Specificity:

- instead of fulfilling Cs by pipetting or chemical reaction before cell sealing
 - use of functionalised **alkali dispensers** from SAES Getters
 - activation of Cs by **local laser heating** of the dispenser



Advantage:

no conflict between the anodic bonding process and Cs chemistry



A. Douahi et al., Elect. Lett, 2007

L. Nieradko et al. Micro/Nanolith. MEMS & MOEMS, 2008

T-cell flow-chart

1. 1.5 mm thick Si wafer + 1 μm thick thermal SiO_2



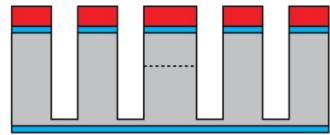
2. Photolithography



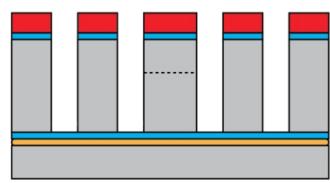
3. SiO_2 etching



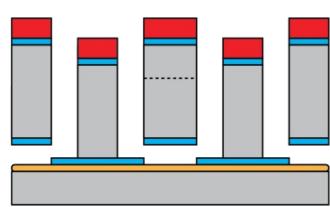
4. 1st DRIE step



5. 2nd DRIE step with oil-bonded holding-wafer



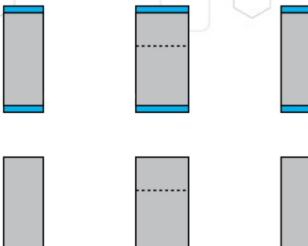
6. Wafer separation and resist stripping



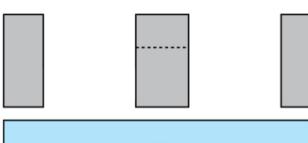
7. O_2 plasma cleaning and KOH polishing



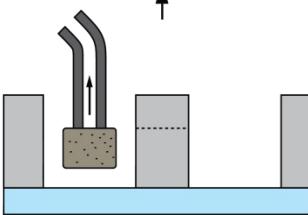
8. SiO_2 stripping in HF



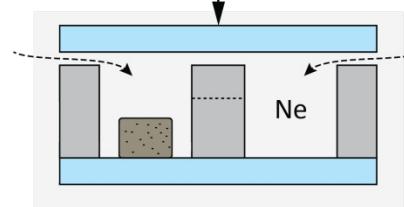
9. 1st anodic bonding



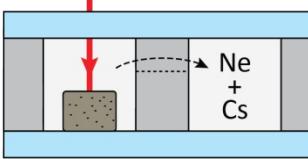
10. Dispenser introduction



11. 2nd anodic bonding under Ne atmosphere

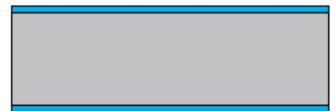


12. Dispenser activation



T-cell flow-chart

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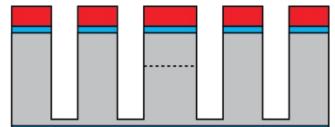
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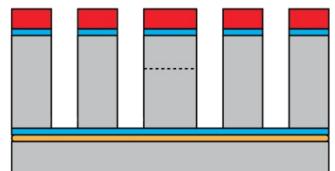
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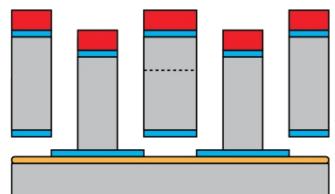
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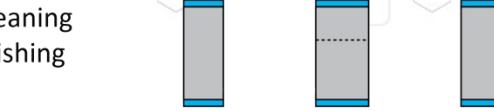
5. 2nd DRIE step with oil-bonded holding-wafer



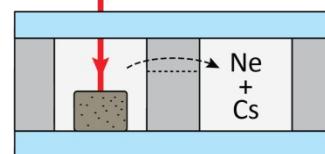
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7. O_2 plasma cleaning and KOH polishing

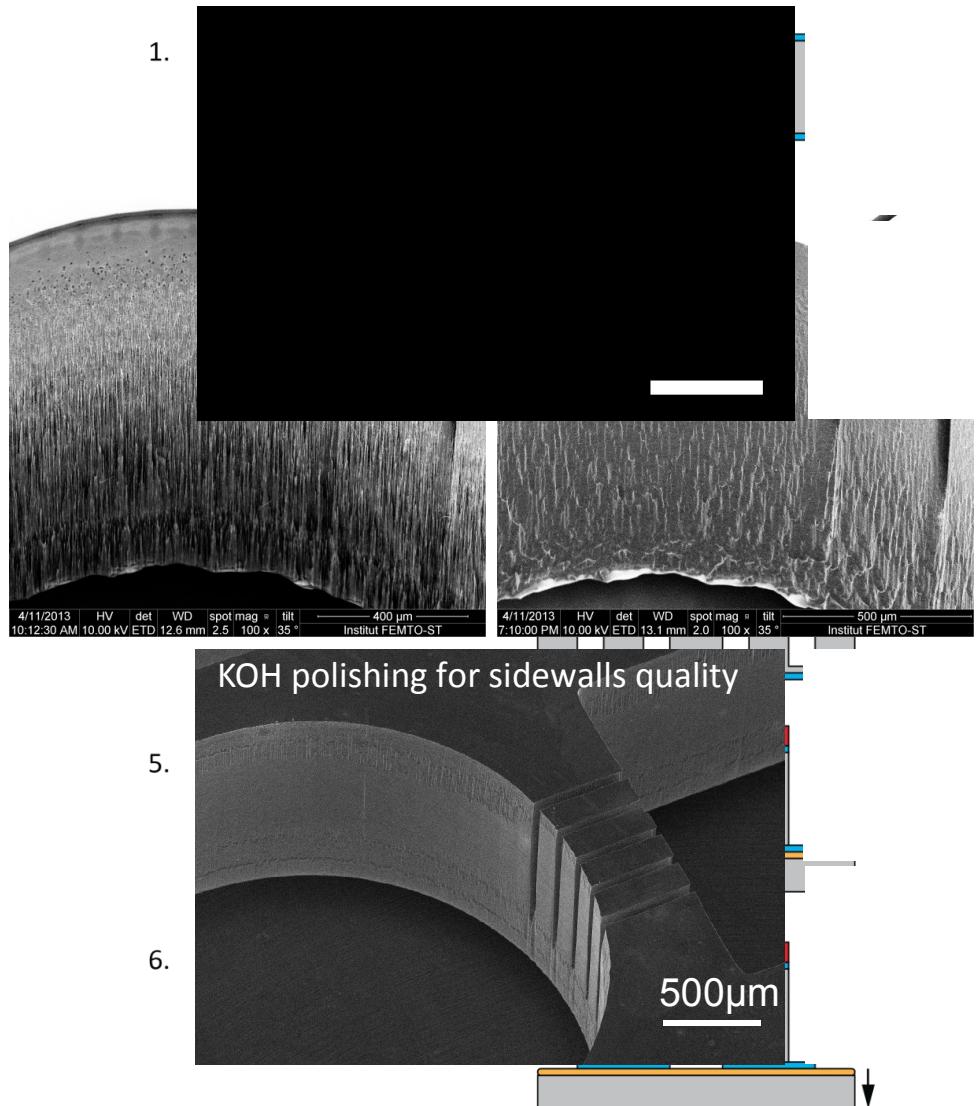


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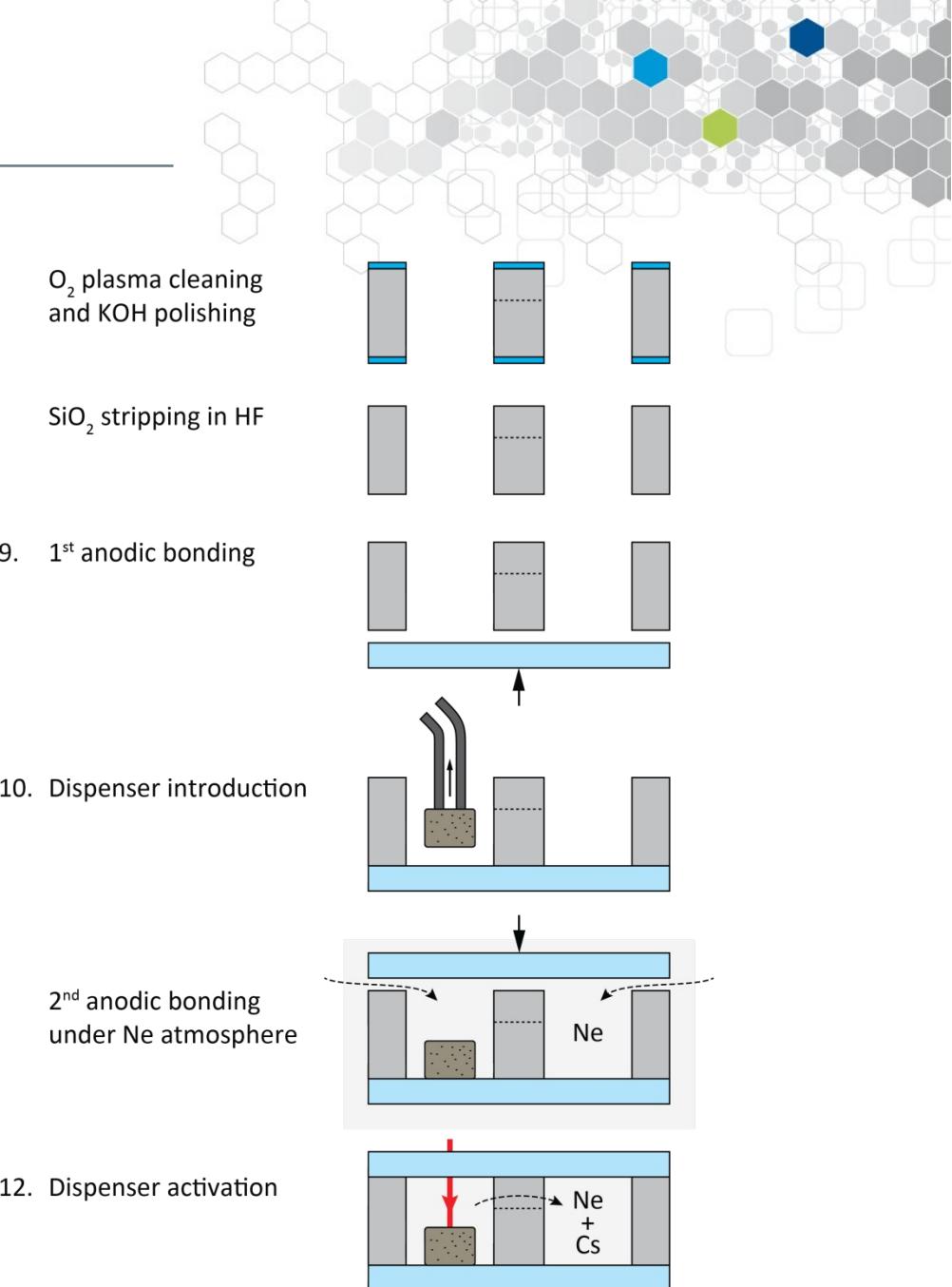


Chutani et al. Sub. Sens Act A 2013

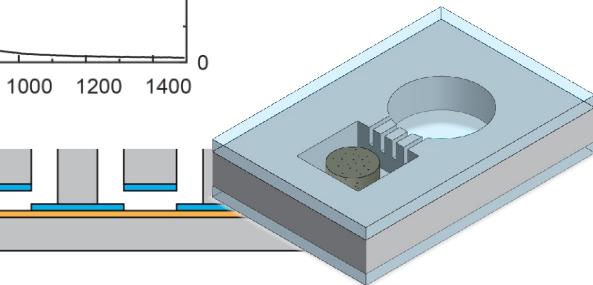
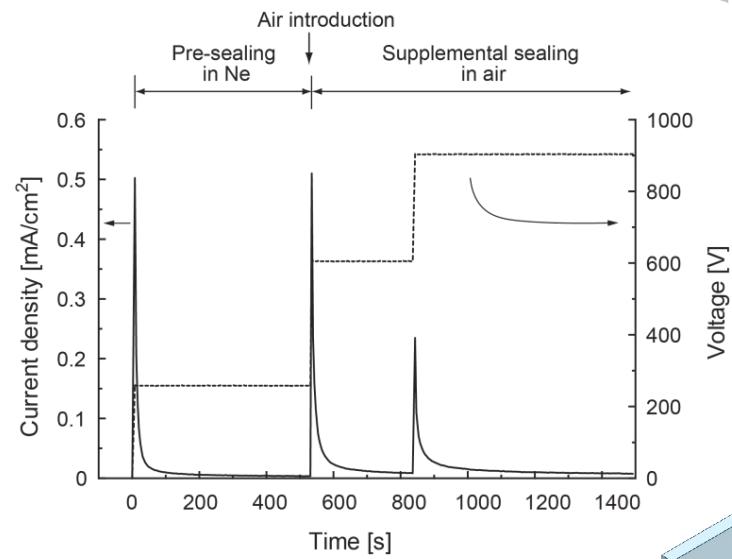
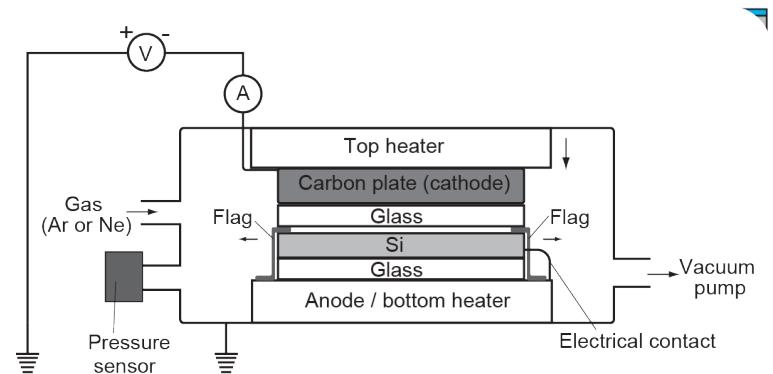
T-cell flow-chart



Chutani et al. Sub. Sens Act A 2013



T-cell flow-chart

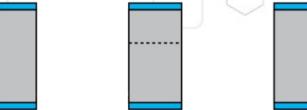


Hasegawa et al., Sens. Act. A, 2011

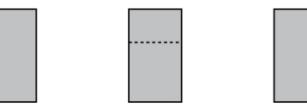
7. O₂ plasma cleaning and KOH polishing



8. SiO₂ stripping in HF

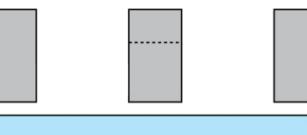


9. 1st anodic bonding

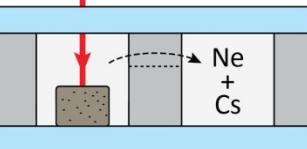
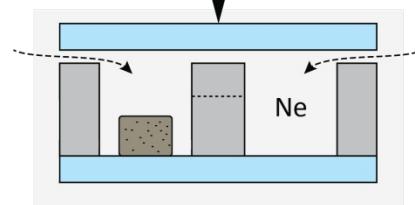


2-steps anodic bonding
→ Pre-sealing in Ne to avoid discharge

10. Dispenser introduction



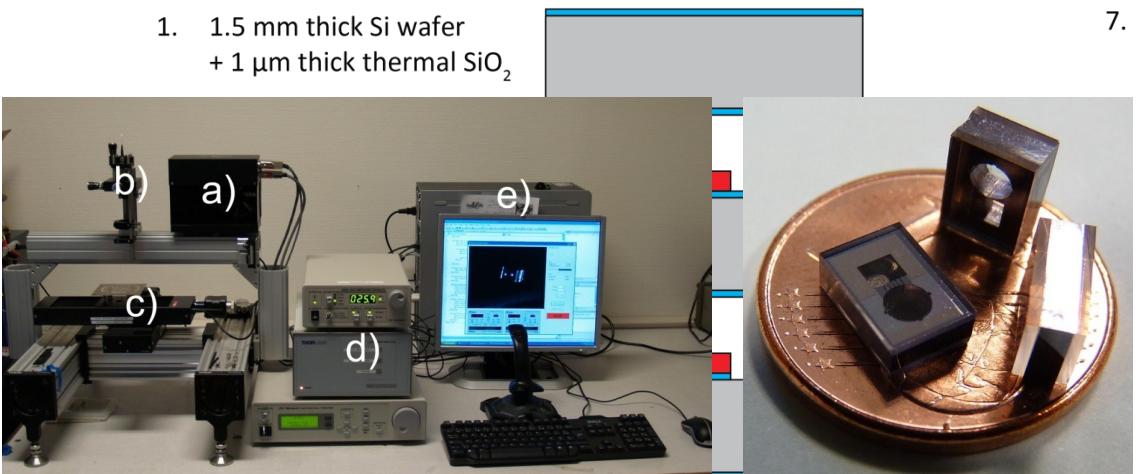
11. 2nd anodic bonding under Ne atmosphere



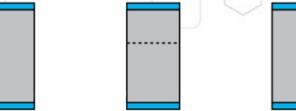
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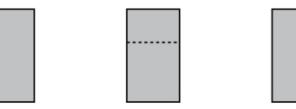
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+ 1 μm thick thermal SiO_2



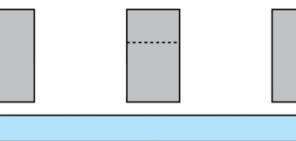
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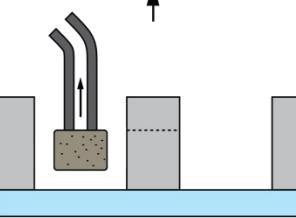
- SiO_2 stripping in HF



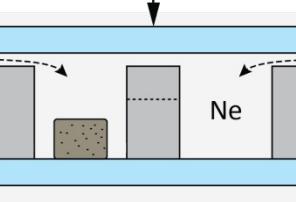
- 1st anodic bonding



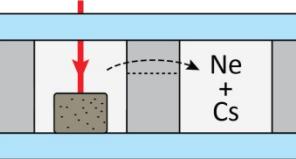
10. Dispenser introduction



11. 2nd anodic bonding
under Ne atmosphere

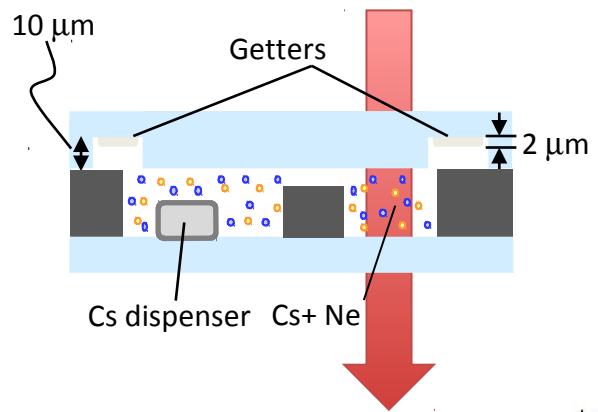
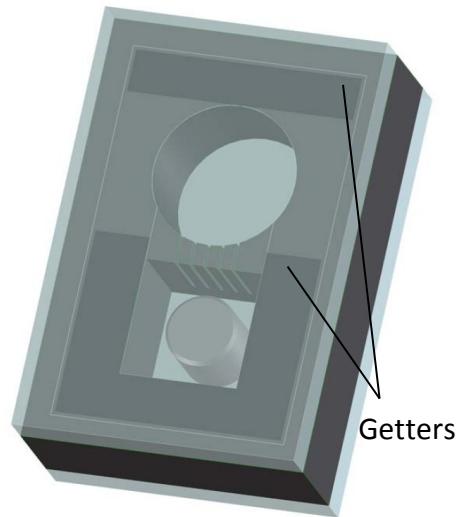


12. Dispenser activation

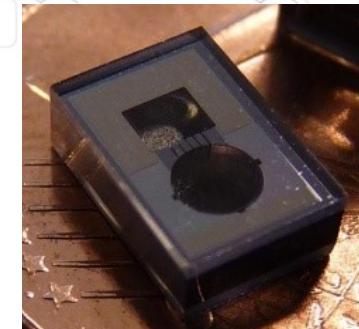


Getters integration

Wafer-level integration technique of getter films SAES PageWafer®



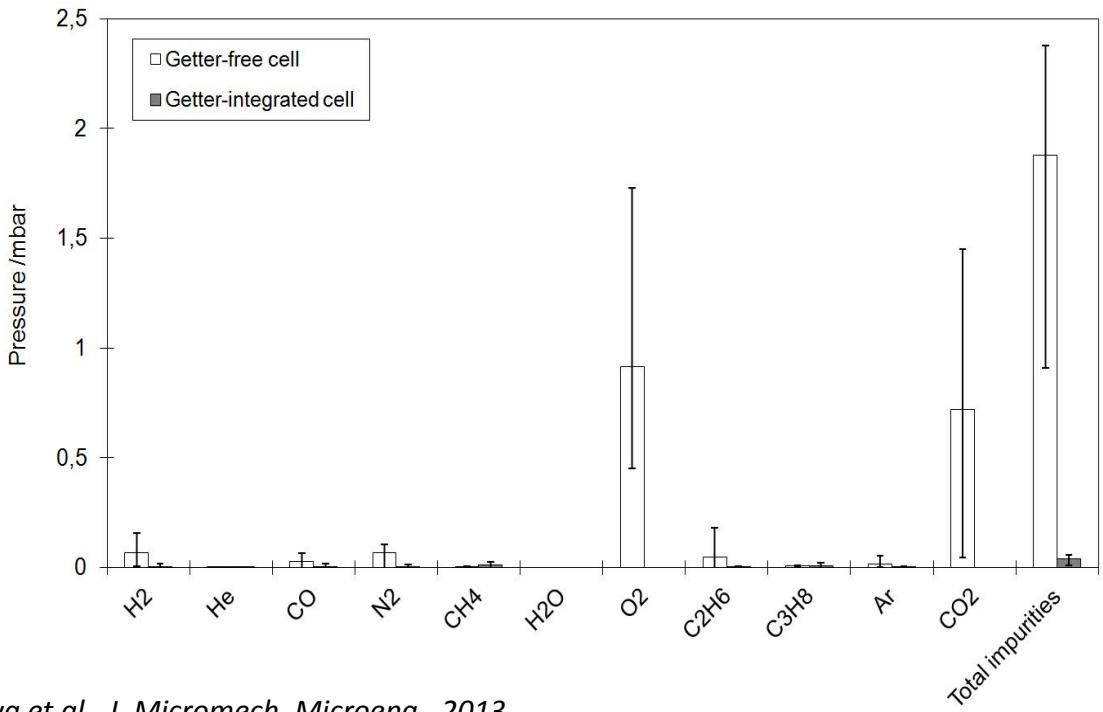
Adsorbs impurities generated during anodic bonding



improvement of the microcell internal atmosphere

50x less impurities without affecting Cs and Ne contents

> 3 years lifetime demonstrated



Hasegawa et al., J. Micromech. Microeng., 2013

A new architecture: R-cell

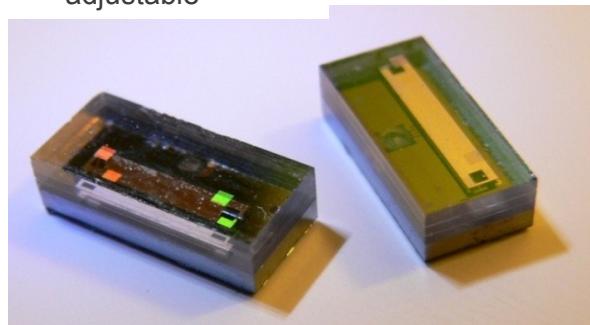
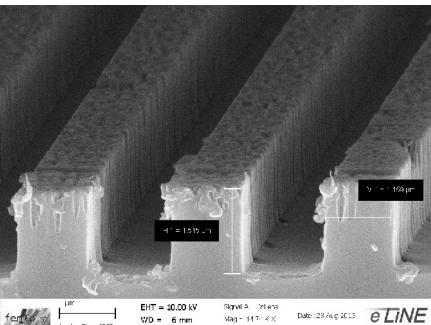
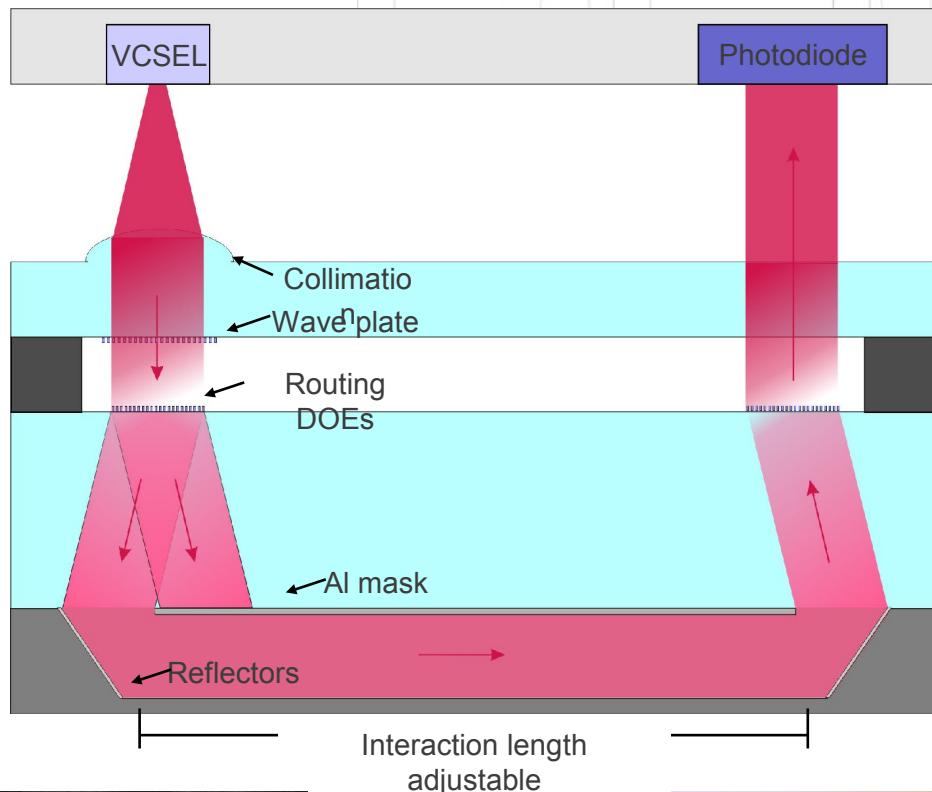
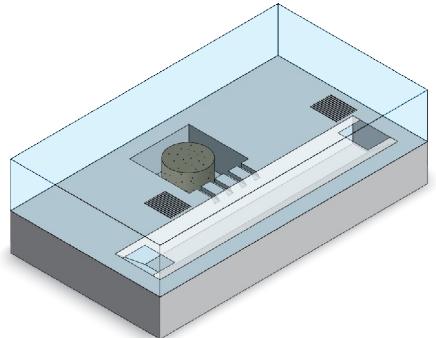


Reflection of light along a Si wet-etched cavity

- Required components:
 - Diffraction gratings for routing
 - Mask for diff-orders discrimination
 - Coatings for efficient reflectors

Strict vertical alignment

- Adjustable optical cavity
- Better thermal control
- Integration of optics **at wafer level**
 - ➡ **Accurate Alignments**
 - Smaller beam diameter
- Laser & detector on the same plane
- ➡ **Reduction of overall thickness**



Passilly et al. Patent 2012

VCSELs for atomic clocks

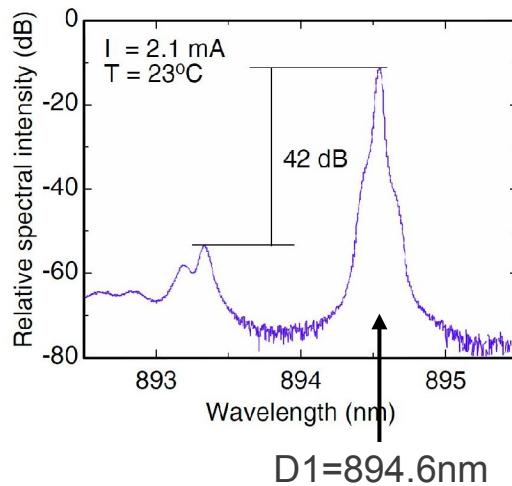
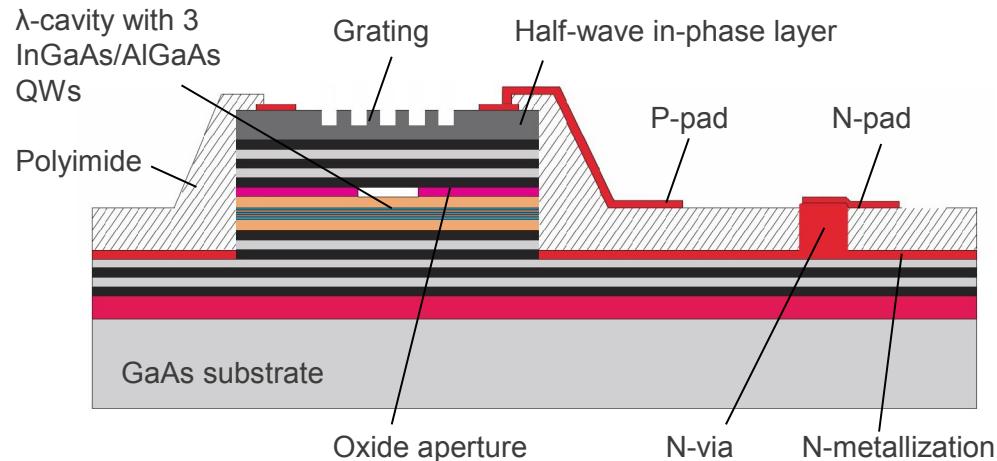


Requirements:

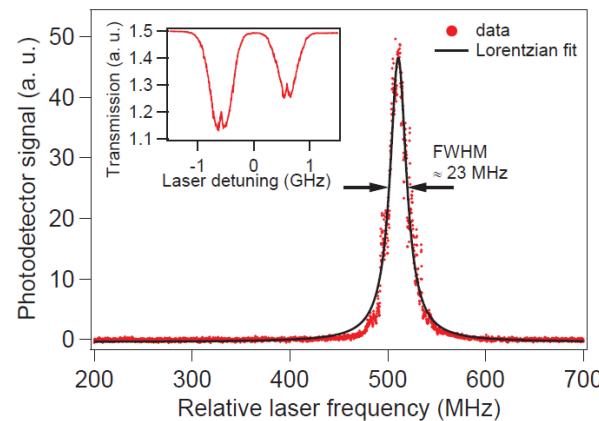
Many!

- **Single mode operation** at a frequency exactly equal to D1 (preferred) or D2 lines
- **Narrow linewidth** Any frequency noise is converted to amplitude noise in the transmission signal
- **High operating temperature** (e.g. 60-80°C)
- **Flip-chip bondable**
- **Single linear polarization** operation
- **Low consumption** Low threshold current (typ. <1mA)
- **Frequency modulation** bandwidth > 4.5GHz

Layout: flip-chip bondable VCSEL



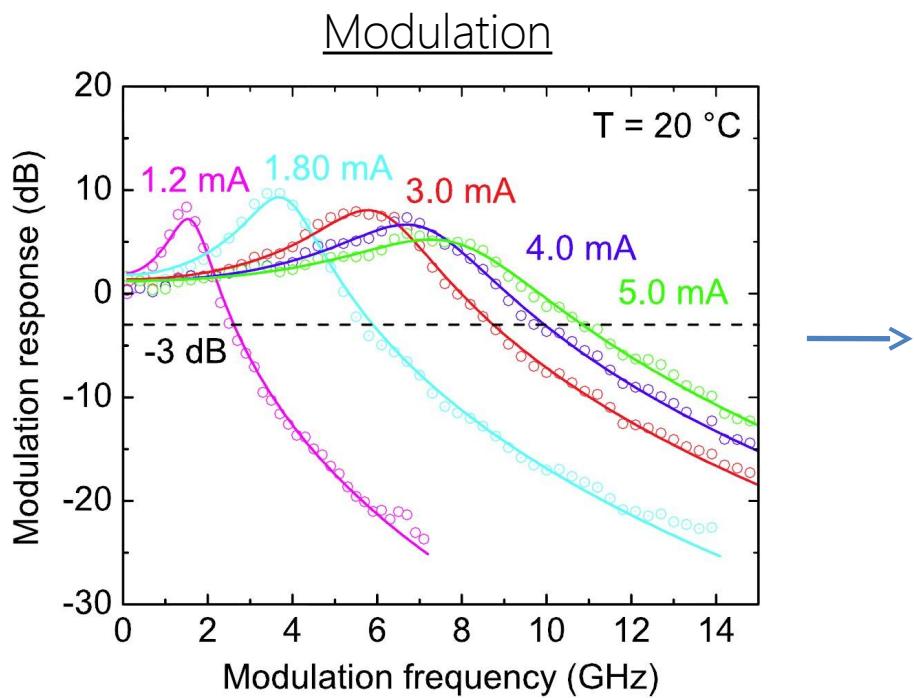
SMSR: 42dB



Linewidth: 20-25MHz
Smaller would be even better

Al-Samaneh et al. IEEE PTL 2011; APL 2012; Miah et al. IEEE JSTQE 2013

Performances



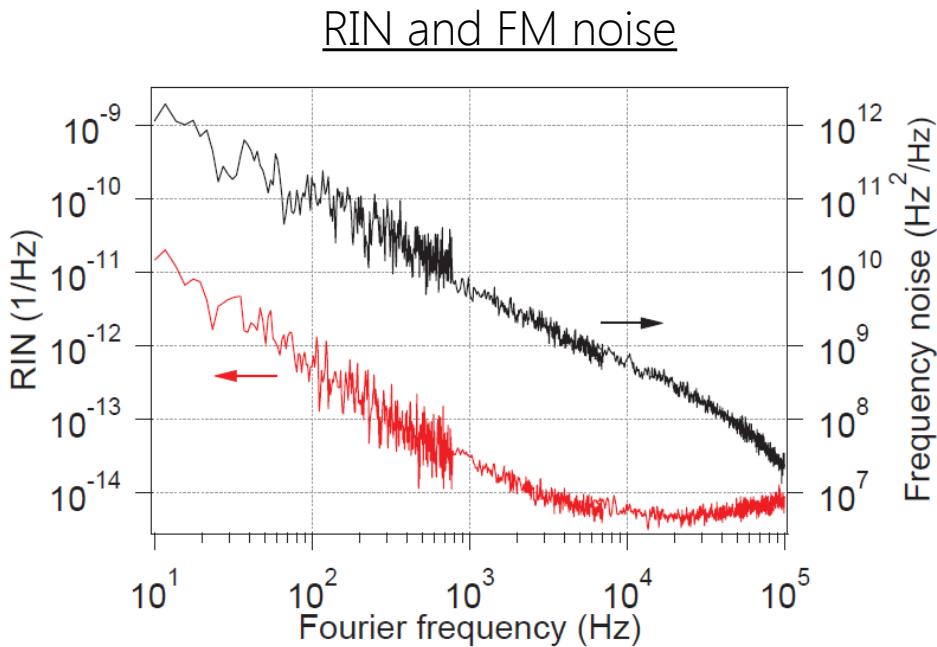
Max 3dB bandwidth of 11.8 GHz obtained at $I=7.0\text{mA}$
Bandwidth of 5.6 GHz obtained at $I=1.8\text{mA}$
(0.9mA above threshold)

RIN: 1.10-11 Hz-1 at 10Hz Fourier Freq. ($P = 700\mu\text{W}$)

VCSEL frequency noise : $10^{13} \cdot f^{-1} \text{Hz}^2/\text{Hz}$ [10Hz;105Hz]

VCSEL Allan deviation: 1.10^{-8} at 1s

Critical for atomic clocks: The VCSEL FM noise is the main limitation to the clock short-term stability.

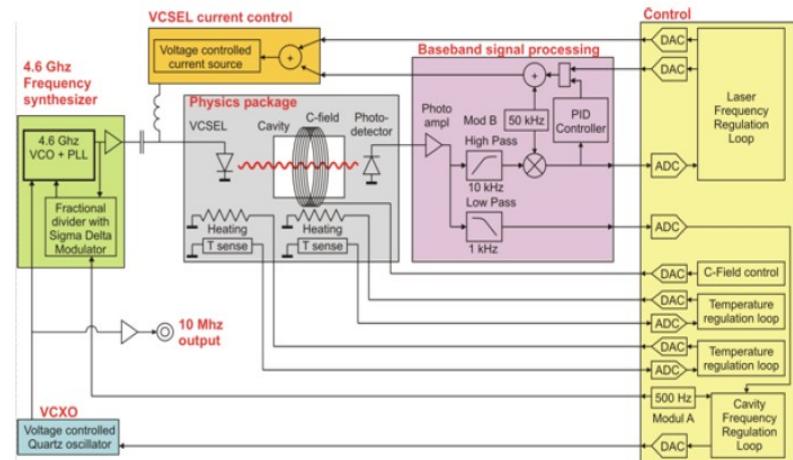


Al-Samaneh et al. IEEE PTL 2011; APL 2012; Miah et al. IEEE JSTQE 2013, F. Gruet et al., Optics Express (2013).

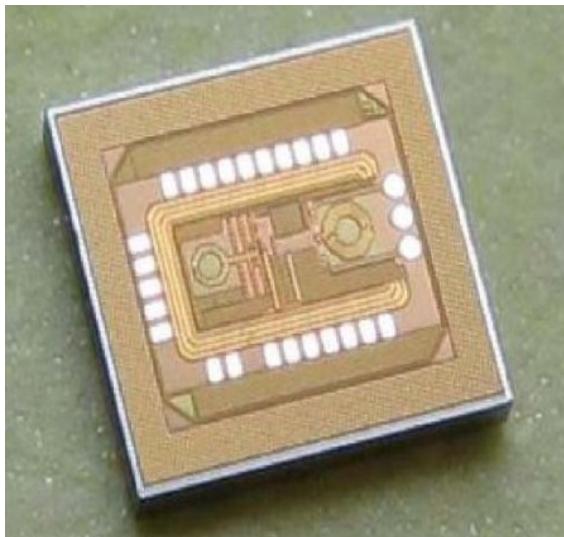
Electronics

Functions:

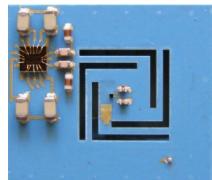
- Cell temperature and B-field control
- Laser current, temperature and frequency stabilization.
- CPT signal reading
- **4.596GHz signal generation and LO frequency servo**



4.596 GHz Local oscillator:



**4.6 GHz LC-VCO phase-locked to a 10 MHz reference
using a N-fractional PLL in a 130 nm CMOS technology ASIC**



Surface footprint = 4mm²
Power consumption = 12 mW
Output power up to 0 dBm to drive the VCSEL
Frequency resolution at the mHz level

Zhao et al., Sub. IEEE TMTT 2013

EPFL
ÉCOLE POLYTECHNIQUE
FÉDÉRALE DE LAUSANNE

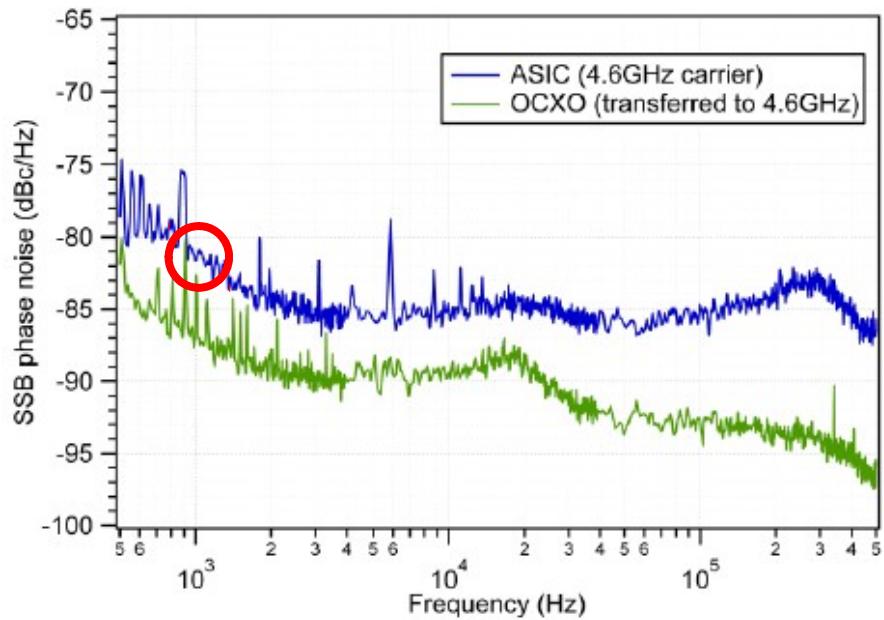
Electronics – Local Oscillator at 4.596 GHz

Dick effect – Intermodulation effect

The short-term stability of the clock can be degraded by the LO phase noise.
 (-80 dBc/Hz at $f = 1 \text{ kHz}$ for 2^{10-11} at 1 s)

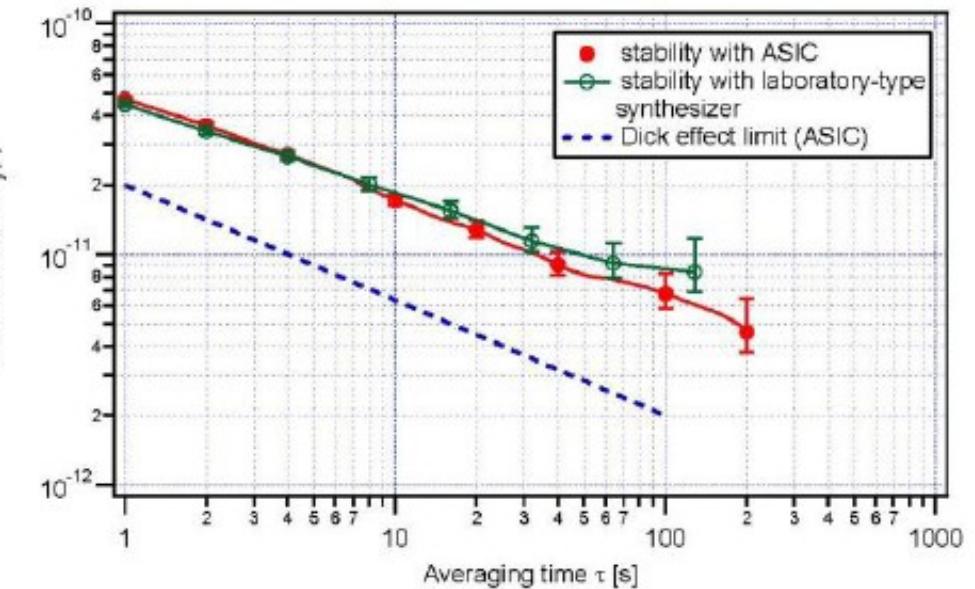
$$\sigma_y(\tau) = \sqrt{\sum_{n=1}^{\infty} C_{2n} \cdot S_{\varphi}(2nf_m) \cdot \tau^{-\frac{1}{2}}}$$

ASIC synthesizer phase noise



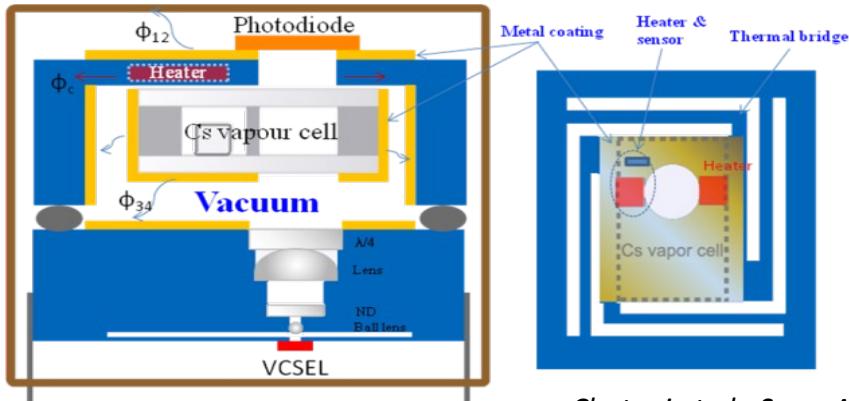
All electronics functions were validated
for miniature clock applications

Short-term stability

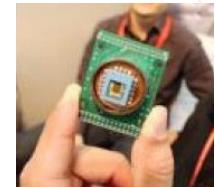


Packaging

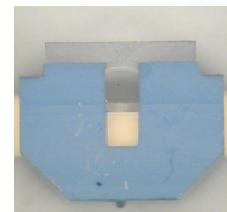
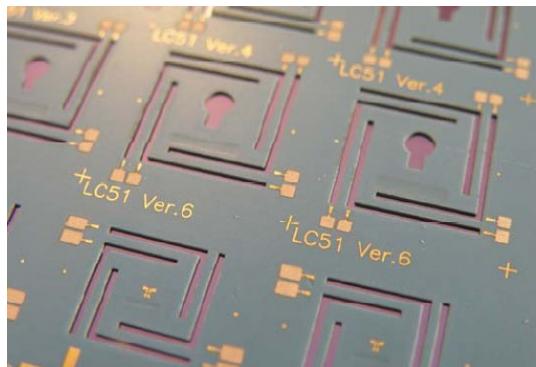
LTCC based package with embedded coils and heaters, vacuum encapsulated



Cell thermal control:
50mK for $T_{ext}=[0,55^{\circ}\text{C}]$



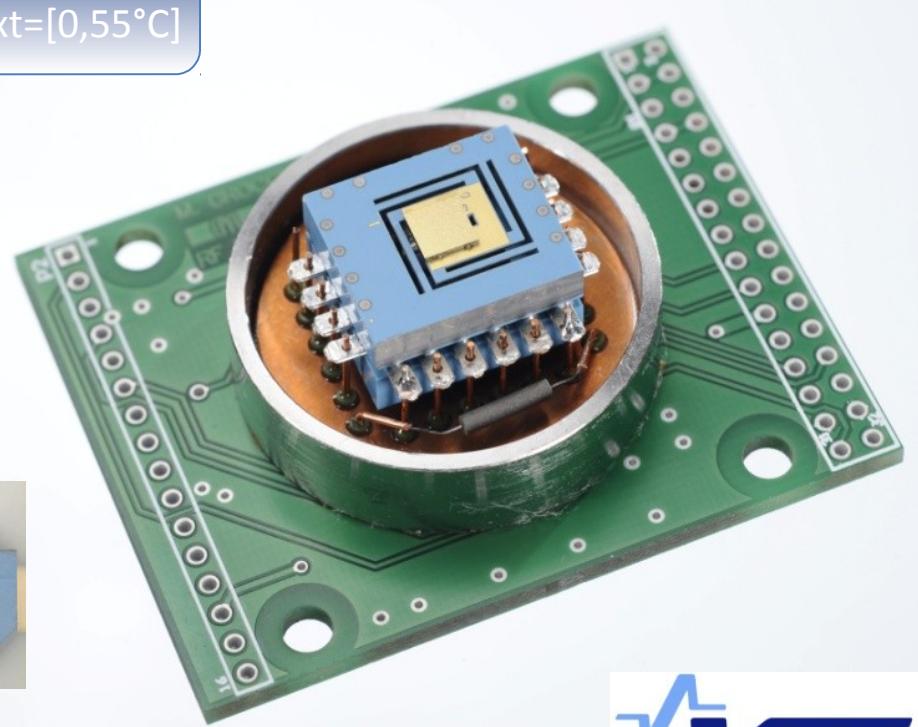
Chutani et al., Sens. Act. A., 2012



Thermally controllable multilayer LTCC platforms

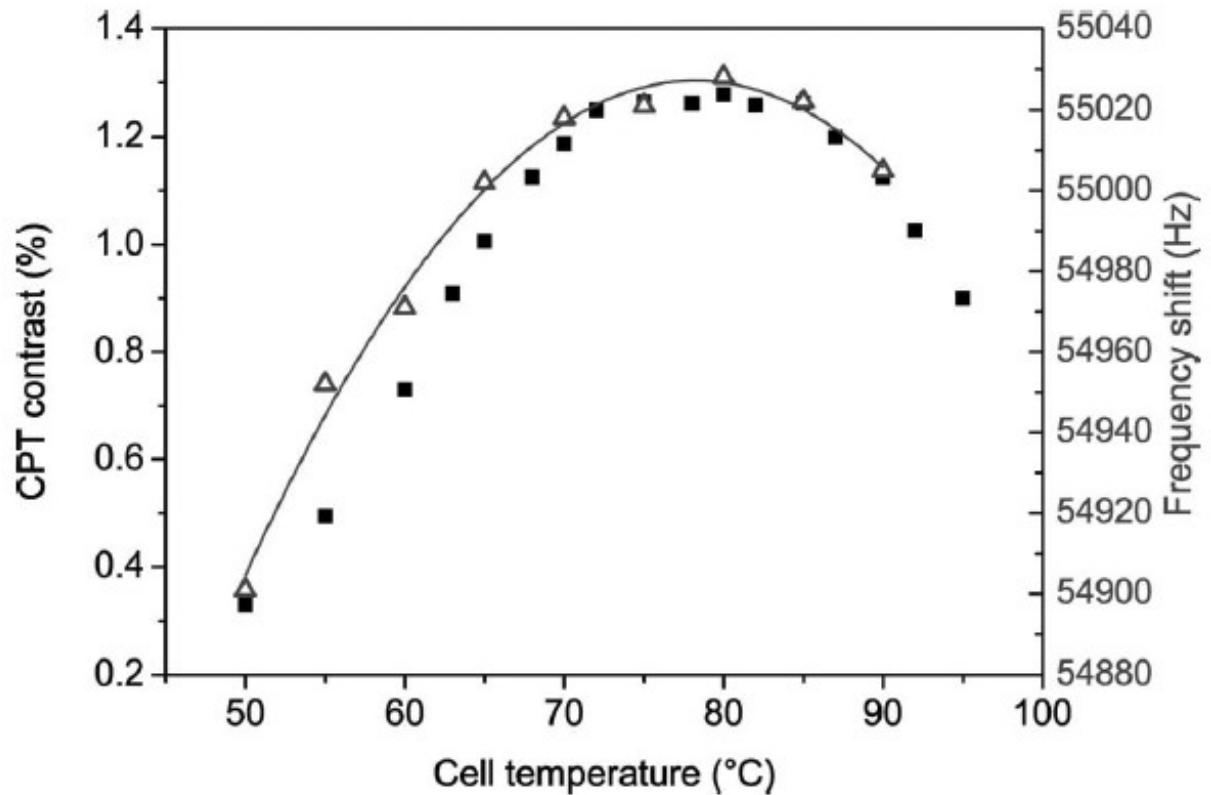
Cs cell subsystem

Optics subsystem



Optimizations: CPT spectroscopy (D1 line)

Cs D1 line is better for CPT interaction



By adjustment of the Ne pressure, the CPT contrast is optimized at 79-80°C where the temperature-dependence is cancelled.

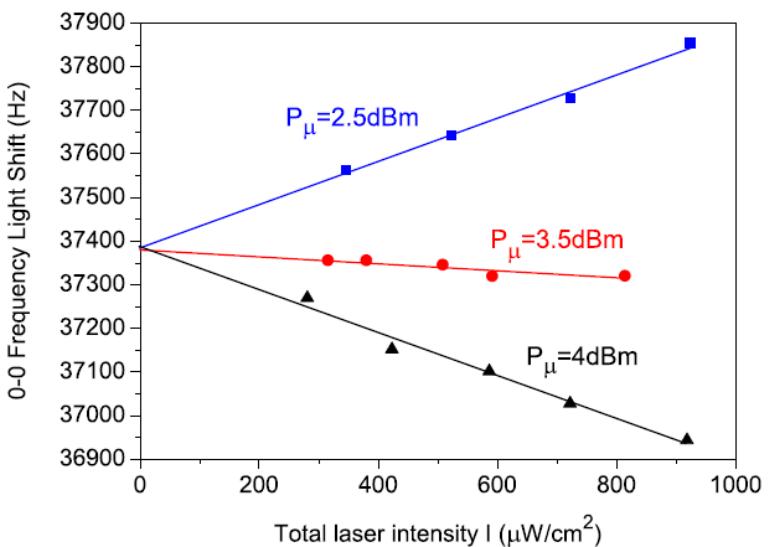
LSC: Light shift cancellation



Light-shift: major effect in CPT clocks → one of the main limitations for long-term performances

↳ **Clock frequency shift** due to laser intensity & frequency variations, sidebands power fluctuations,..

Total light shift can be cancelled by adjusting finely the RF modulation power



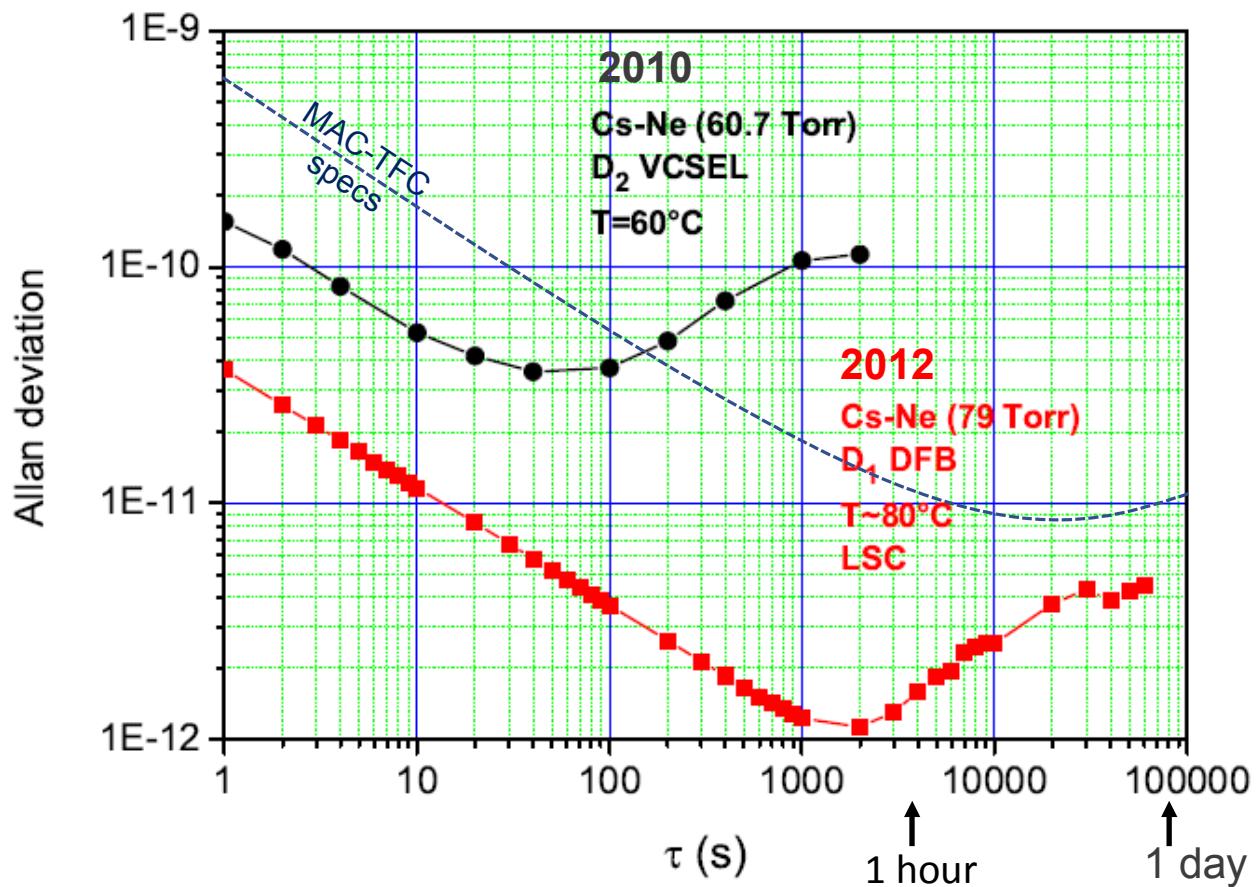
Solution: Find the « magic » zero light-shift point and stabilize the clock operation on this point

R. Boudot et al., J. Appl. Phys. 2012; IEEE UFFC 2012

Frequency Stability Performances

Short-term improved by the use of a laser resonant on the Cs D1 line

Long-term improved by active Light Shift Correction, $T_{cell} \sim 80^\circ\text{C}$, ...



Cs-Ne Microcell
+
laser D1
+
Specific packaging and electronics

Frequency stability better than
 $3 \cdot 10^{-11}$ at 1s
 10^{-11} at 1 day ($1 \mu\text{s}/\text{day}$)

High-performance CPT clocks

R. Boudot et al. IEEE UFFC (2012)



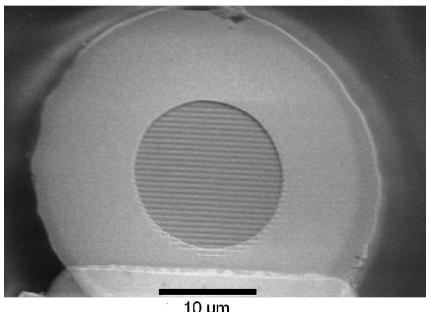
Thanks to all MAC-TFC and ISIMAC partners

Thank you for your attention

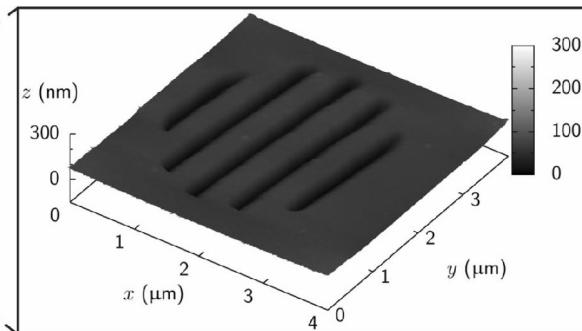
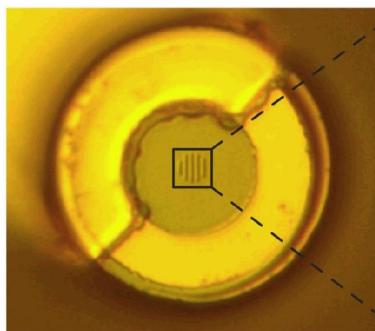
Surface gratings

For polarization stabilization: - Period $d=600\text{nm}$ (sub-wavelength), duty cycle 50%

2 versions:

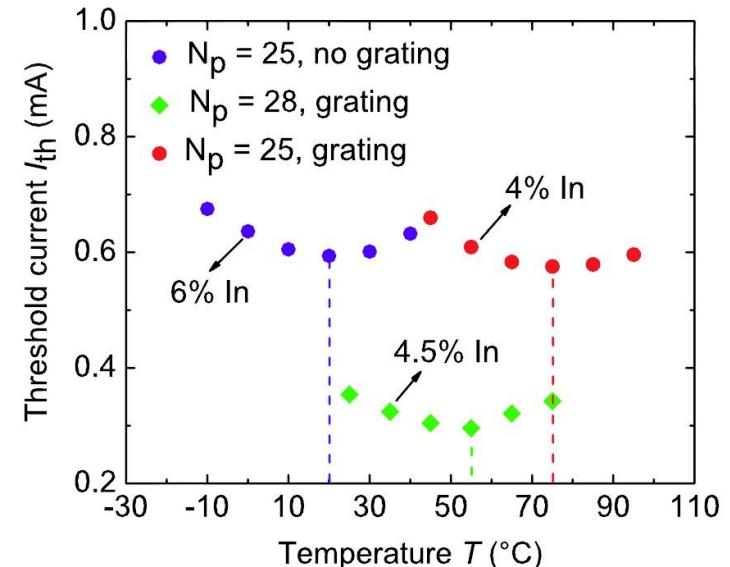


- **V1: large inverted gratings**
(etched in Quarter-wave antiphase layer)
Depth = 70nm
Polarization orth. to gratings line (along [011])

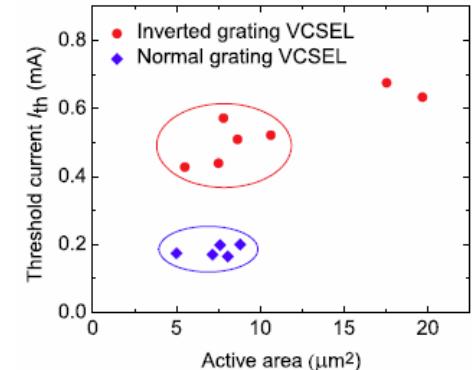


- **V2: $\varphi=3\mu\text{m}$ diameter normal gratings**
(etched in Half-wave in-phase layer)
Depth = 120nm
Polarization paral. to gratings line

Threshold current reduced by
40% compared to inverted
gratings



Tradeoff between N_p and gratings efficiency

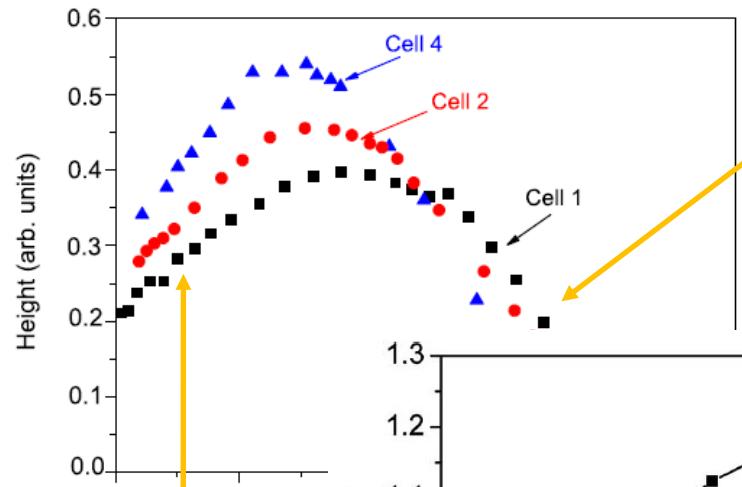


Al-Samaneh et al. IEEE PTL 2011; APL 2012; Miah et al. IEEE JSTQE 2013

CPT spectroscopy (D2 line)

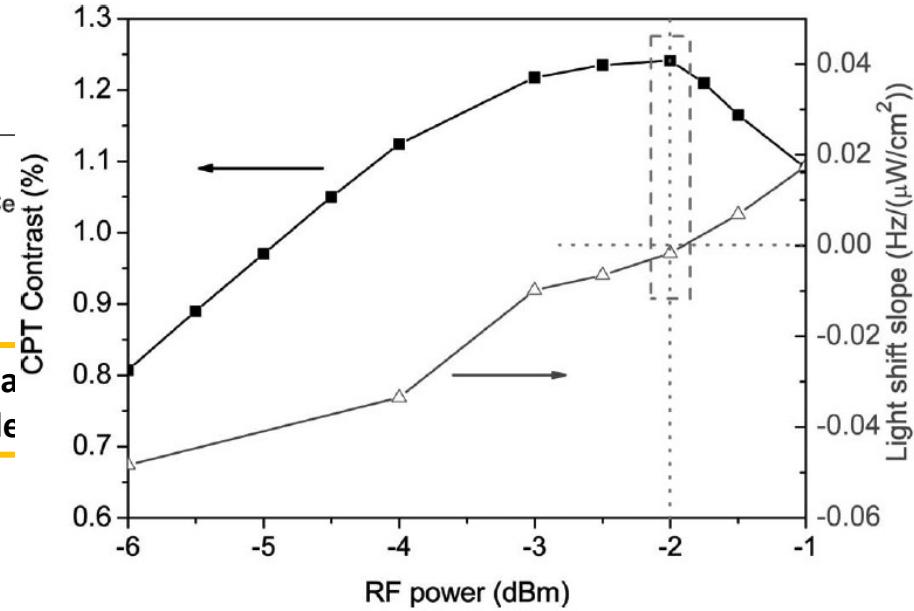


Cell temperature

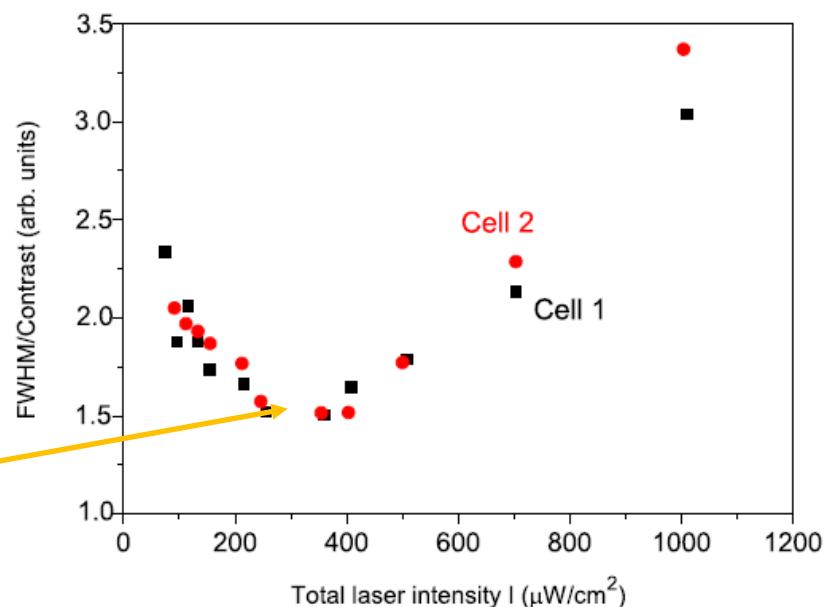


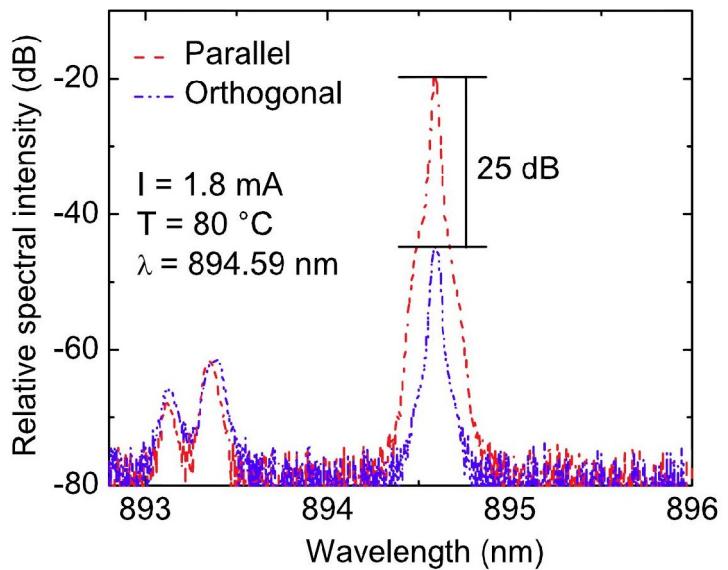
The CPT signal increases with the increase of the Cs density.

The vapor becomes optically thick.

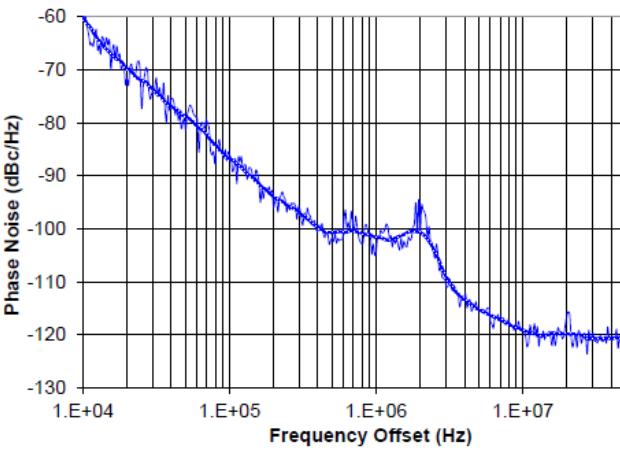


The light shift slope can be cancelled by adjusting the **Laser intensity**.





VCO phase noise



Prospects



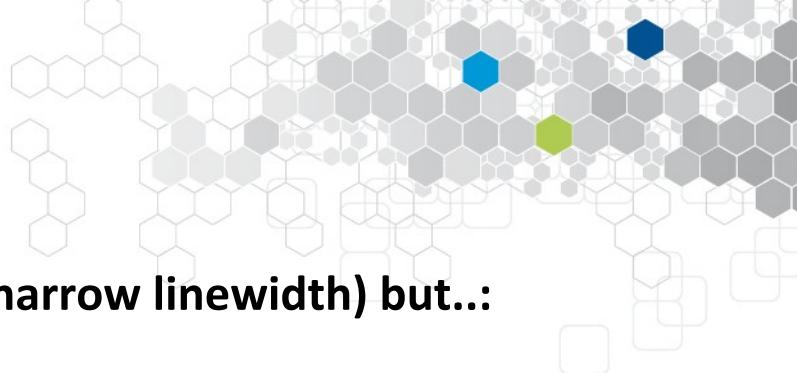
Research studies:

- Optimized CPT pumping schemes with new laser system architectures.
- Anti-relaxation coatings for microfabricated cells.
- New-generation BAW MEMS microwave oscillators.
- New buffer gases for high-temperature operation.

Transfer studies in progress:

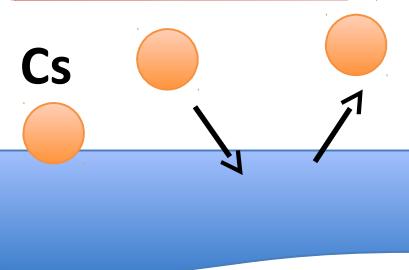
- Microcell technology process.

CPT relaxation mechanisms



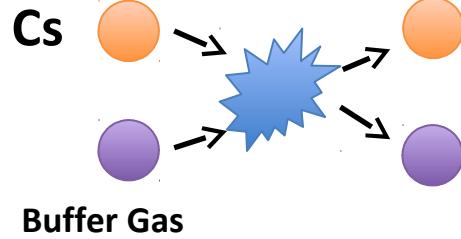
Long CPT coherence relaxation times are needed (for a narrow linewidth) but...:

Collisions to the cell walls



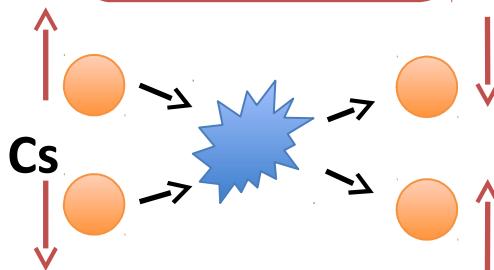
Collision between Cs atoms and the cell walls, the atoms are trapped by the wall and are replaced by a unpolarized atom.

Alkali-buffer gas collisions



Introduce the buffer gas to slow the diffusion of Cs atoms and decreases the CPT resonance linewidth.

Spin exchange



Collision between Cs atoms and Cs atoms cause randomly exchange of electron spins.

FWHM at I=0

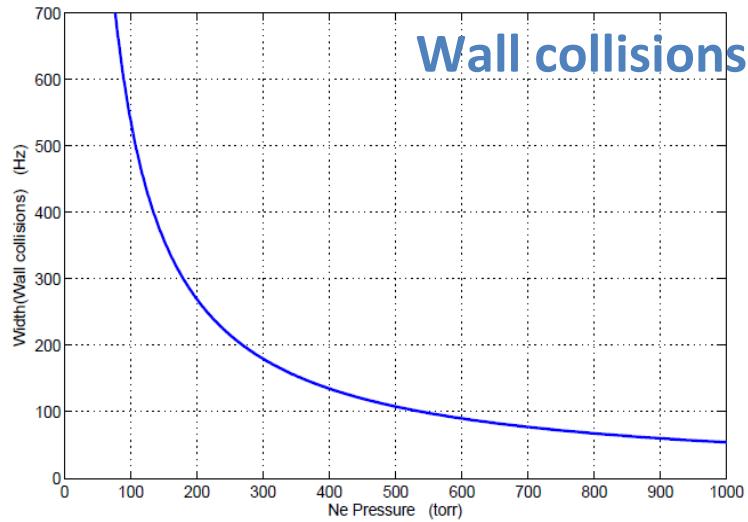
$$\gamma_w = \left[\left(\frac{2.405}{R} \right)^2 + \left(\frac{\pi}{L} \right)^2 \right] D_0 \frac{P_0}{P}$$

$$\gamma_{csbg} = L_0 \bar{v}_{rel} \sigma_{csbg} \frac{P}{P_0}$$

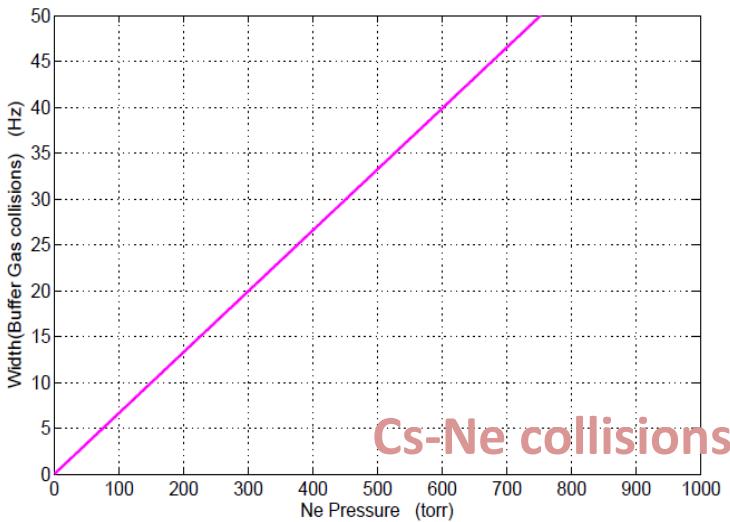
$$\gamma_{se} = \frac{6I+1}{8I+4} \bar{v}_r n_{cs} \sigma_{se}$$

$$\gamma_2 = \gamma_w + \gamma_{se} + \gamma_{csbg}.$$

CPT linewidth with buffer gas pressure

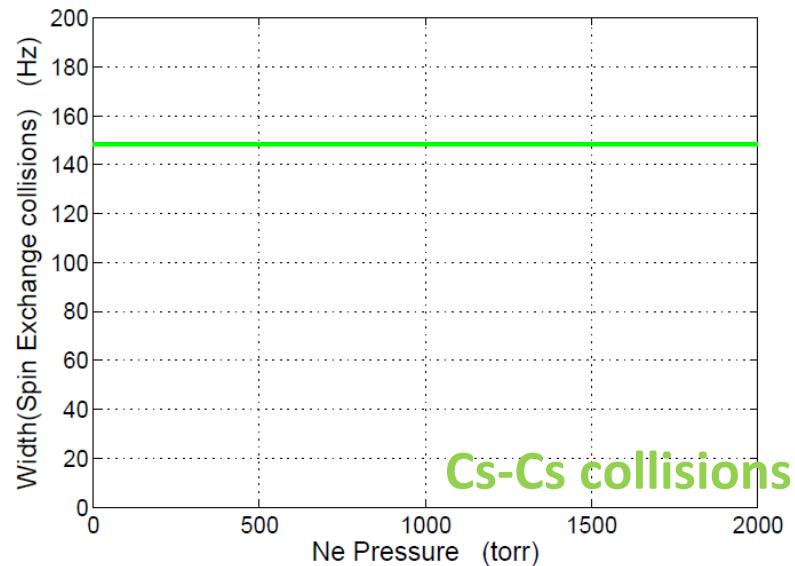


Wall collisions

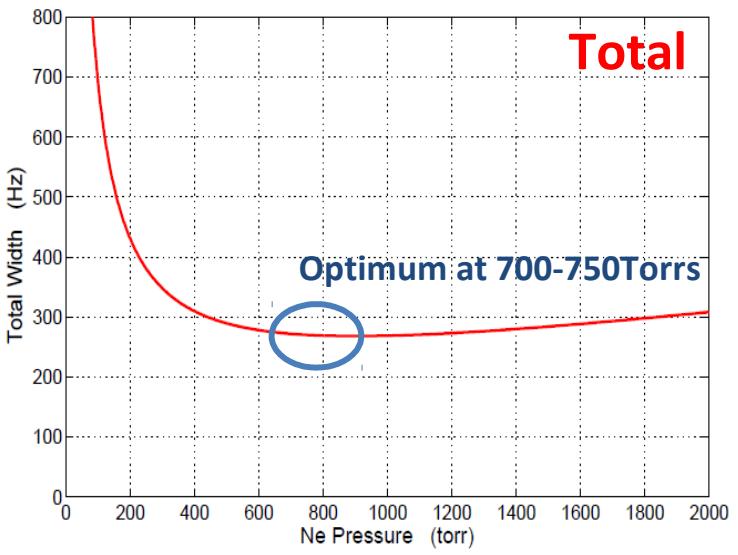


Cs-Ne collisions

Cs-Ne microcell (D=2mm, L=1.4mm, T=60°C)



Cs-Cs collisions



Total

Optimum at 700-750Torr

CPT signal with buffer gas pressure

The presence of buffer gas shifts and broadens optical lines.

Buffer gas	T_1 (K)	γ_1^a (MHz/torr)
He	323	24.13 ± 0.07
^3He	323	26.00 ± 0.05
Ne	313	10.85 ± 0.02
Ar	313	18.31 ± 0.16
Kr	313	17.82 ± 0.05
Xe	313	19.74 ± 0.08
H_2	328	20.81 ± 0.09
HD	318	20.06 ± 0.12
D_2	318	18.04 ± 0.04
N_2	318	15.82 ± 0.05
	323	16.36 ± 0.02
	333	15.66 ± 0.08
CH_4	333	29.00 ± 0.10
C_2H_6	331	26.70 ± 0.03
CF_4	318	18.84 ± 0.05

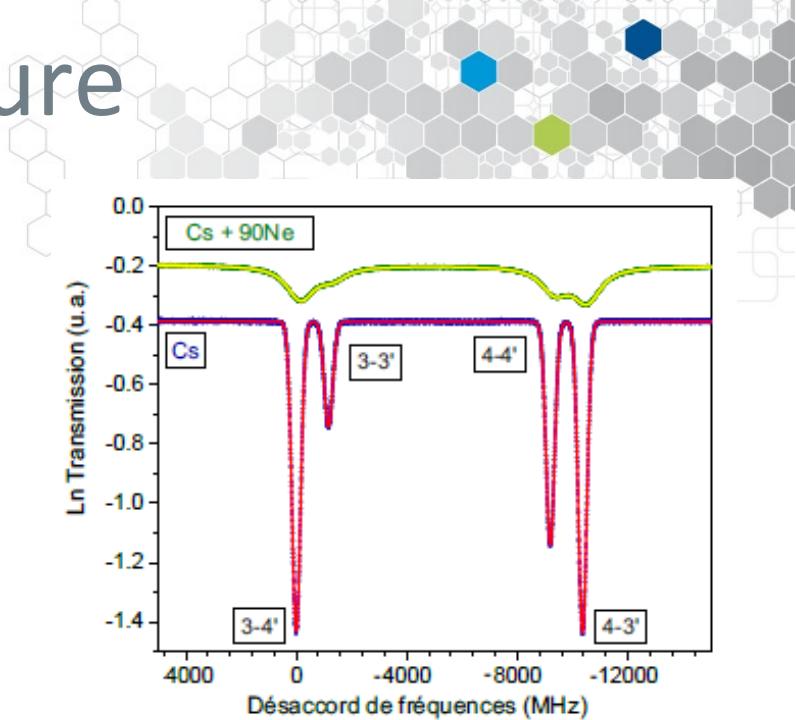
Optical broadening = decrease of optical pumping rate
populating the dark state = reduction of CPT signal.

Buffer gas pressure: trade off signal – linewidth



Broadening coefficients in Cs

G. Pitz et al., PRA 80, 062718 (2009).



O. Kozlova Thesis, LNE-SYRTE (2012)

